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(54) Title: METHODS FOR FORMING A SINGLE CRYSTAL SILICON INGOT WITH REDUCED CRUCIBLE EROSION

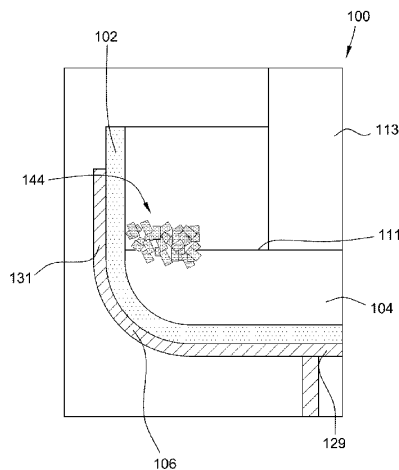


FIG. 4

(57) Abstract: Methods for forming a single crystal silicon ingot with reduced crucible erosion are disclosed. Solid-phase quartz is added to the melt to reduce erosion at the crucible-melt surface interface. The quartz may be synthetic quartz such as synthetic quartz rods. The quartz may be disposed near the crucible-melt surface interface. Quartz dissolves and suppresses the amount of quartz that dissolves from the crucible at the crucible-melt surface interface.

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